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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/082,314	02/26/2002	Fumio Isshiki	ASAM.0053	2802	
38327	7590 06/26/2006		EXAMINER		
REED SMI		GIESY, ADAM			
	IEW PARK DRIVE, SUITE RCH, VA 22042	ART UNIT	PAPER NUMBER		
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			DATE MAILED: 06/26/2006		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Applicat	ion No.	Applicant(s)					
Office Action Summary		10/082,	314	ISSHIKI, FUMIO	- ·				
		Examine	er -	Art Unit					
		Adam R.		2627					
	The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply								
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).									
Status									
1)	Responsive to communication(s) file	d on <i>08 June 2006</i> .							
•	This action is FINAL . 2b)⊠ This action is non-final.								
3) 🗌	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is								
	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.								
Disposition of Claims									
4)🖾	4)⊠ Claim(s) <u>1-18</u> is/are pending in the application.								
	4a) Of the above claim(s) is/are withdrawn from consideration.								
5)	Claim(s) is/are allowed.								
6)⊠	Claim(s) <u>1,3-5,7,8,11 and 14-18</u> is/are rejected.								
•	☑ Claim(s) <u>9,10,12 and 13</u> is/are objected to.								
8)[Claim(s) are subject to restrict	ction and/or election	requirement.						
Applicati	on Papers								
9)🛛	The specification is objected to by th	e Examiner.							
10)⊠ The drawing(s) filed on <u>26 February 2002</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.									
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).								
	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).								
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.									
Priority (ınder 35 U.S.C. § 119								
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 									
	2. Certified copies of the priority documents have been received in Application No								
	3. Copies of the certified copies of the priority documents have been received in this National Stage								
application from the International Bureau (PCT Rule 17.2(a)).									
* See the attached detailed Office action for a list of the certified copies not received.									
Attach	wa)								
Attachment(s) 1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413)									
2) Notic	e of Draftsperson's Patent Drawing Review (F	•	Paper No(s)/Mail D	ate	20.450)				
	nation Disclosure Statement(s) (PTO-1449 or r No(s)/Mail Date	PTO/SB/08)	5) Notice of Informal F 6) Other:	Patent Application (PT	O-152)				

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DETAILED ACTION

Specification

1. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The following title is suggested: Optical Disc Drive Apparatus With a Semiconductor Laser Containing an Asymmetric Quantum Well Structure.

Claim Objections

2. Claim 14 is objected to because of the following informalities:

Examiner suggests that the phrase "...wherein a d.c. drive..." should read "...wherein a d.c. (direct current) drive...".

Appropriate correction is required.

3. Claim 16 is objected to because of the following informalities:

Examiner asserts that the phrase "...claim 1, comprising and a waveband..." should read "...claim 1, comprising a waveband ...".

Appropriate correction is required.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 1, 3.-5, 7, 8, 14, and 18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida US Doc. No. 2002/0024153 A1)

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in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1).

Regarding claim 1, Yoshida discloses an optical head comprising a light source for emitting a light beam (Figure 3, element 301), a lens for focusing the light beam onto a medium (element 302), and a detector for detecting a reflected light beam from the medium (311), the light source having an active layer that is an indirect semiconductor (see page 4, paragraphs 0040-0042). Yoshida fails to disclose that the laser has a barrier layer or that the semiconductor layer contains quantum wells.

Valster discloses an indirect semiconductor laser wherein the light source comprises a semiconductor laser comprising an active layer and a barrier layer (see abstract), said active layer being an indirect semiconductor (see abstract), said indirect semiconductor having a disordered quantum well structure (column 6, lines 38-40). Valster fails to specifically disclose that the quantum well structure is asymmetric.

Sundaram discloses an indirect semiconductor device that contains quantum wells in which the quantum wells are asymmetric (see page 3, paragraph 0034).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam that is more easily controlled by the asymmetric quantum wells.

Regarding claim 3, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that the semiconductor laser has a barrier layer which is also said indirect semiconductor (column 6, lines 21-27 – see especially "Separate Confinement Layers" in lines 24 and 25).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 4, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that said indirect semiconductor is made of an indirect semiconductor mixed crystal material (column 1, lines 15-24).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 5, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida further discloses that

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the optical head is used for reproducing information from the medium (see page 1, paragraphs 0004).

Regarding claim 7, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that the indirect semiconductor has an adjacent confinement structure (column 6, lines 21-27 – see especially "Separate Confinement Layers" in lines 24 and 25).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 8, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Valster further discloses that the material of the indirect semiconductor is of an AlGaP (aluminum, gallium, and phosphor) group (column 6, lines 25-27 – InAlGaP read to be in AlGaP group).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, and the asymmetric nature of the quantum well as disclosed by Sundaram, the motivation being to produce a more intense and direct laser beam.

Regarding claim 14, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida further

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discloses that a d.c. drive is used for driving the semiconductor laser (page 6, paragraph 0061).

Regarding claim 18, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida further discloses an optical disc apparatus (page 3, paragraph 0024).

6. Claim 11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Chapple-Sokol et al. (hereinafter Chapple – US Pat. No. 5,354,707).

Regarding claim 11, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and Sundaram all fail to distinctly disclose that the material of the indirect semiconductor is of a SiGe (silicon germanium) group.

Chapple discloses an indirect semiconductor structure in which the layers are made from the SiGe group (see column 3, lines 11-38 - read to be in the SiGe group).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the layer structure as disclosed by Chapple, the motivation being to produce a more intense and direct laser beam.

7. Claim 15 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Hayashi (US Pat. No. 6,394,655 B1).

Regarding claim 15, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and Sundaram all fail to distinctly disclose that the optical head comprises a multi-layer film reflector provided at an end face of a resonator.

Hayashi discloses that a reflective film is formed at one end face of a resonator in his semiconductor laser (see abstract).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the film and resonator as disclosed by Hayashi, the motivation being to produce a laser with improved transmission speed.

8. Claim 16 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Momoo et al. (hereinafter Momoo - US Pat. No. 6,741,538 B2).

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Regarding claim 16, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and Sundaram all fail to distinctly disclose that the optical head comprises a waveband pass filter for limiting the wavelength of the light beam from the semiconductor laser to be less a half-value width of 2 nm.

Momoo discloses a semiconductor laser system that uses a band-pass filter, in order to limit the reflection and transmission of the light by the wavelength (see column 1, lines 46-48 – this filter can be set to any wavelength for the best mode of operation).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the band-pass filter as disclosed by Momoo, the motivation being in order to limit the reflection and transmission of the light by the wavelength.

9. Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshida et al. (hereinafter Yoshida – US Doc. No. 2002/0024153 A1) in view of Valster et al. (hereinafter Valster – US Pat. No. 5,296,717) and further in view of Sundaram et a. (hereinafter Sundaram – US Doc. No. 2004/0195509 A1) and even further in view of Brown (US Pat. No. 5,625,729).

Regarding claim 17, Yoshida, Valster, and Sundaram disclose all of the limitations of claim 1 as discussed in the claim 1 rejection above. Yoshida, Valster, and

Sundaram all fail to distinctly disclose that the optical head comprises a cooler for lowering the temperature of a light emitting part of the semiconductor laser.

Brown discloses a semiconductor laser with heat sinks or active coolers for lowering the temperature of the light emitting part of the laser during operation (see column 14, lines 20-34).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the optical head structure as disclosed by Yoshida, the layering structure and quantum wells as disclosed by Valster, the asymmetric nature of the quantum well as disclosed by Sundaram, and the cooler as disclosed by Brown in order to effectively avoid overheating the light emitting part of the laser.

Allowable Subject Matter

10. Claims 9, 10, 12, and 13 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

See reasons for indicating allowable subject matter in the Office Action that was mailed on 4/4/2005.

Conclusion

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Adam R. Giesy whose telephone number is (571) 272-7555. The examiner can normally be reached on 8:00am- 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, William R. Korzuch can be reached on (571) 272-7589. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a

USPTO Customer Service Representative or access to the automated information

system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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